

Dual N-channel TrenchMOS standard level FET 23 April 2013 Pi

Product data sheet

### 1. General description

Dual standard level N-channel MOSFET in a LFPAK56D package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V<sub>GS(th)</sub> > 1 V @ 175 °C

### 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Table 1. Quie	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; Tmb = 25 °C; <u>Fig. 1</u>		-	-	27	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	32	W
Static characte	eristics FET1 and FET2						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>		-	21.25	25	mΩ
Dynamic characteristics FET1 and FET2							
Q <sub>GD</sub>	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 20 \text{ V};$ $T_j = 25 \text{ °C}; \text{Fig. 14}; \text{Fig. 15}$		-	2.6	-	nC

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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		 S1 G1 S2 G2
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1		

# 6. Ordering information

Table 3. Ordering in	formation						
Type number	Package						
	Name	Description	Version				
BUK7K25-40E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205				

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7K25-40E	72540E

# 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	40	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS}$ = 20 k $\Omega$ ; $T_j \ge 25 \text{ °C}$ ; $T_j \le 175 \text{ °C}$	-	40	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC	-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; Tmb = 25 °C; <u>Fig. 1</u>	-	27	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	-	19	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4	-	107	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	32	W
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#### **Dual N-channel TrenchMOS standard level FET**

Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drain	diode FET1 and FET2		-	1	1	
l <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	27	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	107	А
Avalanche Ruggedness FET1 and FET2						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_{D} = 28 \text{ A}; V_{sup} \le 40 \text{ V}; V_{GS} = 10 \text{ V};$ $T_{j(init)} = 25 \text{ °C}; \underline{Fig. 3}$	[1][2]	-	10	mJ

[1] Refer to application note AN10273 for further information

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

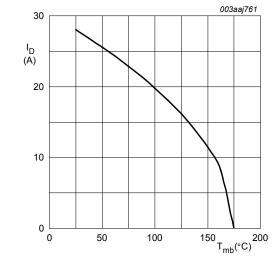
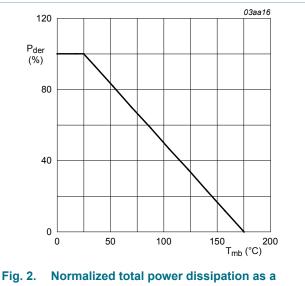


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$ 

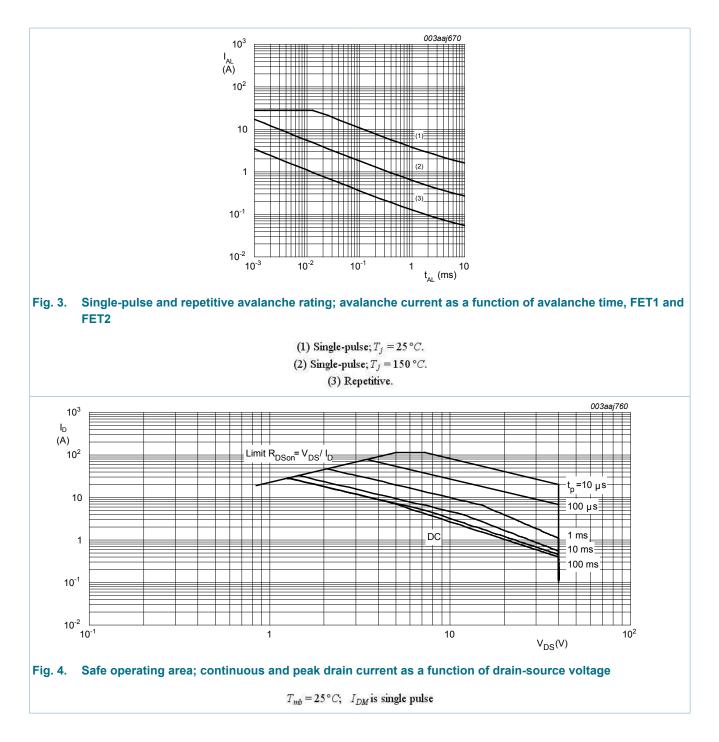


function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

# BUK7K25-40E

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### 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	-	4.68	K/W

# BUK7K25-40E

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ymbol	Parameter	Condition	S		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient			Minimum footprint; mounted on a printed circuit board		-	95	-	K/W
(K/W) 1							003aaj557	
10-1					P		$\delta = \frac{t_p}{T}$	
10 <sup>-2</sup>	ngle shot	10 <sup>-4</sup>	10 <sup>-3</sup>	10 <sup>-2</sup>	10 <sup>-1</sup>	$t_p \leftarrow T \rightarrow T$		

### **10. Characteristics**

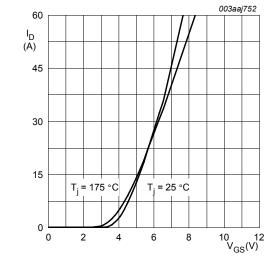
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics FET1 and FET2	· · ·				
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	36	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	40	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 10; Fig. 11	2.4	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 10; Fig. 11	1	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; Fig. 10; Fig. 11	-	-	4.5	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	21.25	25	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 13	-	40.1	49.3	mΩ

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Dynamic cl	haracteristics FET1 and FE	T2					
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 5 A; $V_{DS}$ = 32 V; $V_{GS}$ = 10 V;		-	7.9	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 14;</u> <u>Fig. 15</u>		-	1.5	-	nC
Q <sub>GD</sub>	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 20 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 14}; \text{ Fig. 15}$		-	2.6	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C		-	394	525	pF
C <sub>oss</sub>	output capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>		-	107	128	pF
C <sub>rss</sub>	reverse transfer capacitance			-	76	104	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 32 V; R <sub>L</sub> = 6.5 Ω; V <sub>GS</sub> = 10 V;		-	4.4	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C; I_D = 5 A$		-	4.5	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	8.3	-	ns
t <sub>f</sub>	fall time	-		-	5.2	-	ns
Source-dra	in diode FET1 and FET2	1	11				
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 5 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 17</u>		-	0.78	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 5 A; d $I_{S}$ /dt = -100 A/µs; V <sub>GS</sub> = 0 V;		-	12.4	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C		-	6.7	-	nC





 $V_{DS} = 10V$ 

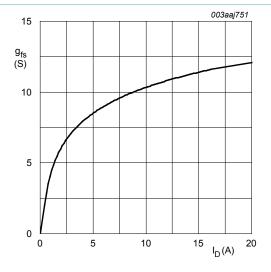
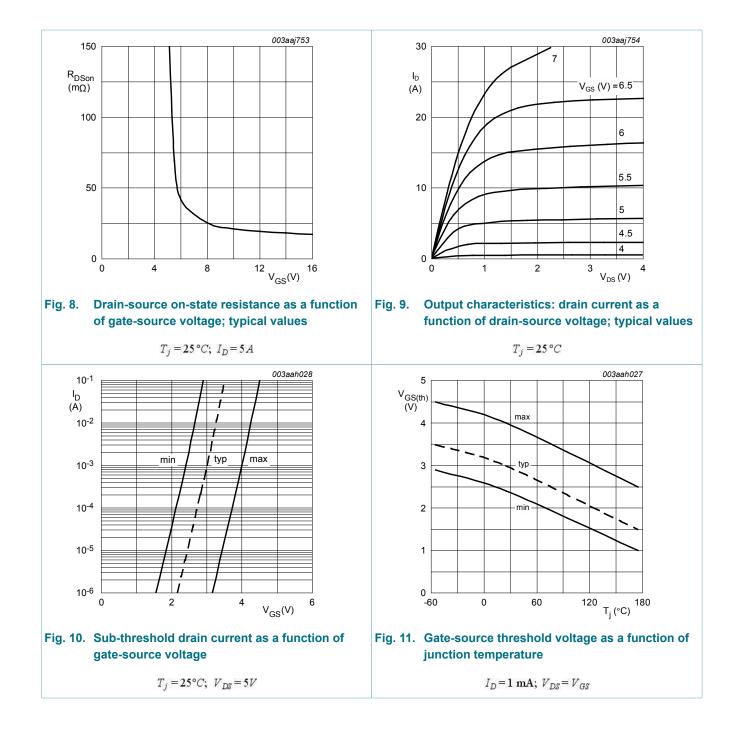


Fig. 7. Forward transconductance as a function of drain current; typical values

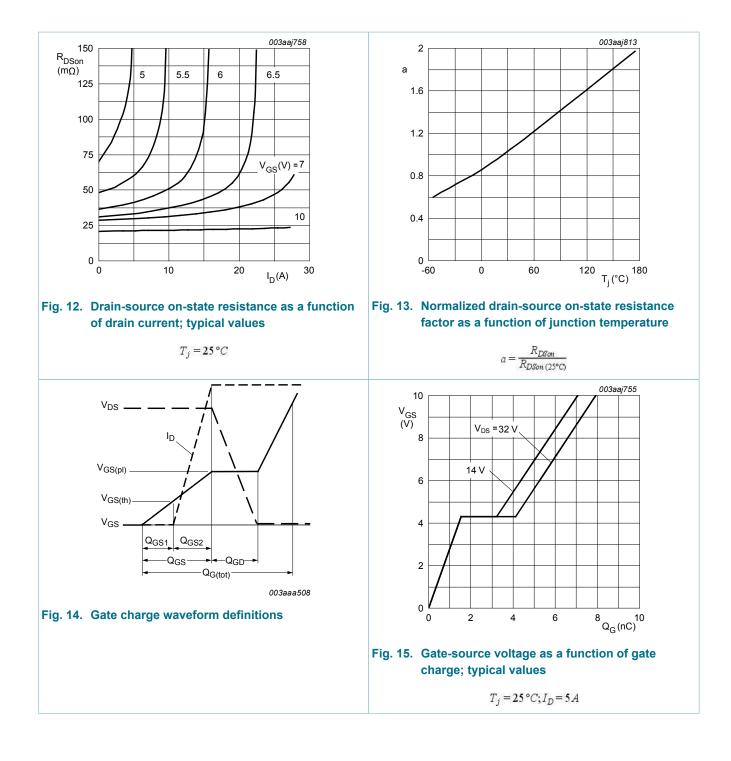
 $T_j = 25 \,^{\circ}C; V_{DS} = 15 \, V$ 

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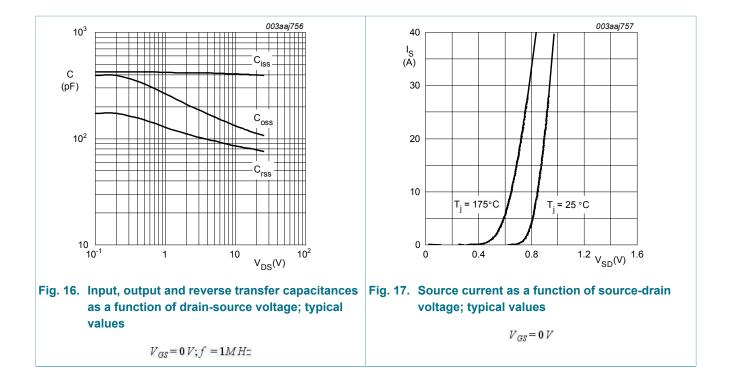
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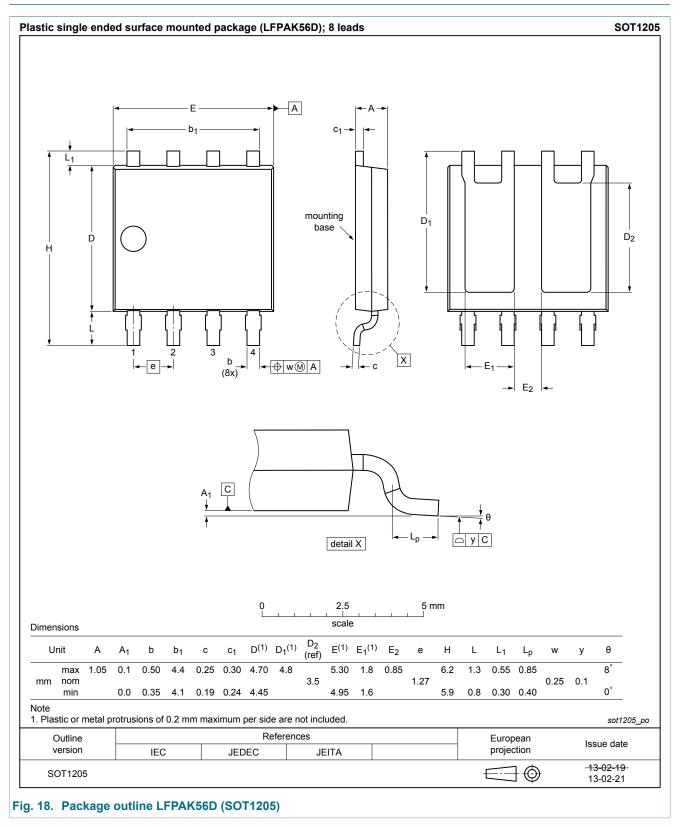
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#### **Dual N-channel TrenchMOS standard level FET**

### **11. Package outline**



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#### **Dual N-channel TrenchMOS standard level FET**

### 13. Contents

1	General description1
2	Features and benefits1
3	Applications1
4	Quick reference data 1
5	Pinning information2
6	Ordering information2
7	Marking2
8	Limiting values2
9	Thermal characteristics4
10	Characteristics5
11	Package outline 10
12	Legal information11
12.1	Data sheet status 11
12.2	Definitions11
12.3	Disclaimers11
12.4	Trademarks 12

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